

C-MOS QUAD SPST ANALOG SWITCH

■ GENERAL DESCRIPTION

The NJU201A is a quad break-before-make SPST analog switch protected up to 44V operating voltage.

All switches are controlled by TTL or C-MOS compatible input.

The low on-state resistance is about half compare with the NJU7301.

The NJU201A is functionally and pin-to-pin compatible with SILICONIX DG201A.

■ PACKAGE OUTLINE



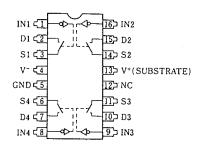
NJU201AD

NJU201AM

■ FEATURES

- High Break Down Voltage -- 44V
- Low On-state Resistance
- Package Outline
- DIP/DMP 16
- C-MOS Technology

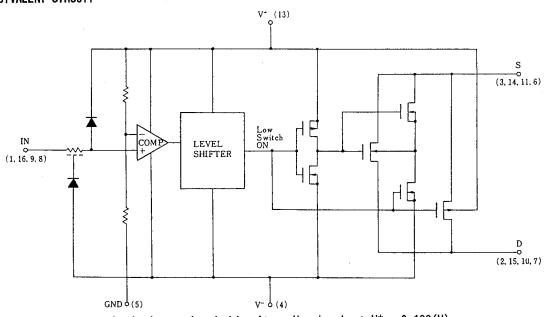
■ PIN CONFIGURATION



TRUTH TABLE

Logic (In)	Switch
0	ON
1	OFF

EQUIVALENT CIRCUIT



* Logic input threshold voltage $V_{\rm TH}$ is about V^+ x 0.128(V). When the designing, enough margin is required.

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■ TERMINAL DESCRIPTION

No.	SYMBOL	FUNCTION	No.	SYMBOL	FUNCTION		
1	IN1	Control Signal Input	9	1 N3	Control Signal Input		
2	D1	Innut /0t 1	10	D3	1		
3	S1	Input/Output 1	11	S 3	Input/Output 3		
4	V-	Negative (V ⁻) Power Supply	12	NC	Non Connection		
5	GND	Ground	13	V ⁺	Positive (V ⁺) Power Supply		
6	S4	lanut (Outract A	14	S2	1 1/0 1 1 0		
7	D4	Input/Output 4	15	D2	Input/Output 2		
8	1 N4	Control Signal Input	16	1N2	Control Signal Input		

■ ABSOLUTE MAXIMUM RATINGS

(Ta=25℃)

	1		u-200 /
PARAMETER	SYMBOL	RATINGS	UNIT
	V+ - V-	44	
Supply Voltage	V+ - GND	19	٧
	GND - V-	25	
Input Voltage	V _I ,V _S ,V _D	V ⁻ -0.5 ~ V ⁺ +0.5 *	٧
	I	30	
Input Current	Is,ID Continuous	20	mA
	Peak Value (PW=1ms,Duty0.1)	70	
Power Dissipation	P⊅	500 (DIP)/ 200 (DMP)	mW
Operating Temperature Range	Topr	0 ~+ 70	Ç
Storage Temperature Range	Tstg	- 65 ~ + 125	ပ

^{*} $V^++0.5V$ must be 44V or less.



■ ELECTRICAL CHARACTERISTICS (DC CHARACTERISTICS)

($V^{+}=15V$, $V^{-}=-15V$, GND=0V)

	OVIDOL	CONDITIONS		TYP		MAX		UNIT	
PARAMETER	SYMBOL CONDIT		1110119	25℃	0℃	25℃	70℃	UNII	
Analog Signal Range	Vanalog			±15		±15	±15	٧	
0 11 0 11	D	V _{1N} =0.8V	V _D =10V	50	100	100	125	Ω	
On-state Resistance	Ron	ls=-1mA	V _D =-10V	50	100	100	125		
Source-off	1 ((()	V0 4V	Vs=14V,VD=-14V	0.01		5	100		
Leakage Current	ls(off)	ff) V ₁ =2.4V	Vs=-14V,VD=14V	-0.02		- 5	-100	nA	
Drain-off	l _D (off)	. ()	V0 4V	V _D =14V,V _S =-14V	0.01		5	100	
Leakage Current		V ₁ =2.4V	V _D =-14V, V _S =14V	-0.02		- 5	-100	nA	
Drain-on	. , ,	V =0 0V	V _D =V _S =14V	0.1		5	200	nA:	
Leakage Current	l _⊅ (on)	V ₁ =0.8V	VD=VS=-14V	-0.15		- 5	-200	IIA	
		V1=2.4V		-0.0004		- 1	- 10		
Input Current	IH	V :=15V		0.003		1	10	μA	
	l _{IL}	V1=0V		-0.0004		- 1	- 10		
	. 1+	V:=0 or 2.4V		0.9		2		mA	
Quiescent Current	I-			-0.3		- 1			

SWITCHING CHARACTERISTICS

 $(V^{+}=15V, V^{-}=-15V, GND=0V)$

	SYMBOL CONDITION			TYP	MAX			шит	
PARAMETER			IIIUNS	25°C	0℃	25℃	70℃	UNIT	
Turn-on Time	ton	D =11.0	0 =25	480		600		n o	
Turn-off Time	toff	R _L =1kΩ, G _L =35pF		370		450		ns	
Charge Injection	Q	C_L =1000pF, V_{GEN} =0V, R_{GEN} =0 Ω		20				рС	
Source-Off Capacit.	Cs(off)		Vs=0V, V1=5V	5					
Drain-Off Capacit.	CD(off)	f=100kHz	£=1001.11=	V _D =0V, V _I =5V	5				рF
Channel-On Capacitance	C _D (on) +C _S (on)		V _D =V _S =0V, V ₁ =0V	16				PΓ	
Off Isolation	OIRR	V =0V	f=100LU=	70				dB	
Channel-to-channel Crosstalk	CCRR	$V_{\rm S}$ =2 $V_{\rm P-P}$, f=100kHz, $R_{\rm L}$ =75 Ω	90				uв		

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MEMO

[CAUTION]
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